



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the Application of: **INOUE, et al.**

Group Art Unit: 2814

Serial No.: **09/473,988**

Examiner: **DOAN, Theresa T.**

Filed: **December 29, 1999**

P.T.O. Confirmation No.: 1714

For. **SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME**

PRELIMINARY AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Date: July 8, 2003

Sir:

Prior to continued examination, please amend the above-captioned patent application as follows:

IN THE CLAIMS:

Please amend claims 1 and 8 as follows:

1. (Five Times Amended) A semiconductor device comprising an insulating interlayer formed on a conductive film, said insulating interlayer including:
a first insulating layer of a composition containing SiH;
a second insulating layer formed on said first insulating layer; and
a third insulating layer formed between said conductive film and said first insulating layer,
wherein said first insulating layer has an H content of not less than 15.4 atom% in the

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